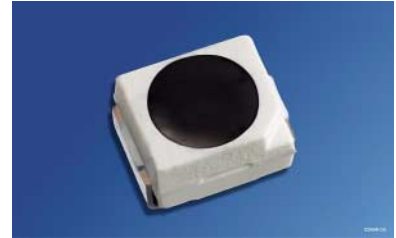


NPN-Silizium-Fototransistor im SMT TOPLED®-Gehäuse
Silicon NPN Phototransistor in SMT TOPLED®-Package
Lead (Pb) Free Product - RoHS Compliant

SFH 320
SFH 320 FA



SFH 320



SFH 320 FA

Wesentliche Merkmale

- Speziell geeignet für Anwendungen im Bereich von 380 nm bis 1150 nm (SFH 320) und bei 880 nm (SFH 320 FA)
- Hohe Linearität
- P-LCC-2 Gehäuse
- Gruppiert lieferbar
- Für alle Lötverfahren geeignet.

Anwendungen

- Miniaturlichtschranken für Gleich- und Wechsellichtbetrieb
- Industrieelektronik
- „Messen/Steuern/Regeln“

Features

- Especially suitable for applications from 380 nm to 1150 nm (SFH 320) and of 880 nm (SFH 320 FA)
- High linearity
- P-LCC-2 package
- Available in groups
- Suitable for all soldering methods.

Applications

- Miniature photointerrupters
- Industrial electronics
- For control and drive circuits

Typ Type	Bestellnummer Ordering Code	Typ Type	Bestellnummer Ordering Code
SFH 320	Q65110A2471	SFH 320 FA	Q65110A2472
SFH 320-3	Q65110A2469	SFH 320 FA-3	Q65110A2470
SFH 320-3/-4	Q65110A1781	SFH 320 FA-3/-4	Q65110A2475
SFH 320-4	Q65110A2510	SFH 320 FA-4	Q65110A1836

Grenzwerte
Maximum Ratings

Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Betriebs- und Lagertemperatur Operating and storage temperature range	$T_{op}; T_{stg}$	- 40 ... + 100	°C
Kollektor-Emitterspannung Collector-emitter voltage	V_{CE}	35	V
Kollektorstrom Collector current	I_C	15	mA
Kollektorspitzenstrom, $\tau < 10 \mu s$ Collector surge current	I_{CS}	75	mA
Verlustleistung, $T_A = 25 \text{ }^\circ\text{C}$ Total power dissipation	P_{tot}	165	mW
Wärmewiderstand für Montage auf PC-Board Thermal resistance for mounting on pcb	R_{thJA}	450	K/W

Kennwerte ($T_A = 25\text{ °C}$, $\lambda = 950\text{ nm}$)

Characteristics

Bezeichnung Parameter	Symbol Symbol	Wert Value		Einheit Unit
		SFH 320	SFH 320 FA	
Wellenlänge der max. Fotoempfindlichkeit Wavelength of max. sensitivity	$\lambda_{S\max}$	980	980	nm
Spektraler Bereich der Fotoempfindlichkeit $S = 10\%$ von S_{\max} Spectral range of sensitivity $S = 10\%$ of S_{\max}	λ	450 ... 1150	750 ... 1120	nm
Bestrahlungsempfindliche Fläche ($\varnothing 220\text{ }\mu\text{m}$) Radiant sensitive area	A	0.038	0.038	mm^2
Abmessung der Chipfläche Dimensions of chip area	$L \times B$ $L \times W$	0.45×0.45	0.45×0.45	$\text{mm} \times \text{m}$ m
Halbwinkel Half angle	φ	± 60	± 60	Grad deg.
Kapazität, $V_{CE} = 0\text{ V}$, $f = 1\text{ MHz}$, $E = 0$ Capacitance	C_{CE}	5.0	5.0	pF
Dunkelstrom Dark current $V_{CE} = 20\text{ V}$, $E = 0$	I_{CEO}	1 (≤ 50)	1 (≤ 50)	nA

Die Fototransistoren werden nach ihrer Fotoempfindlichkeit gruppiert und mit arabischen Ziffern gekennzeichnet.

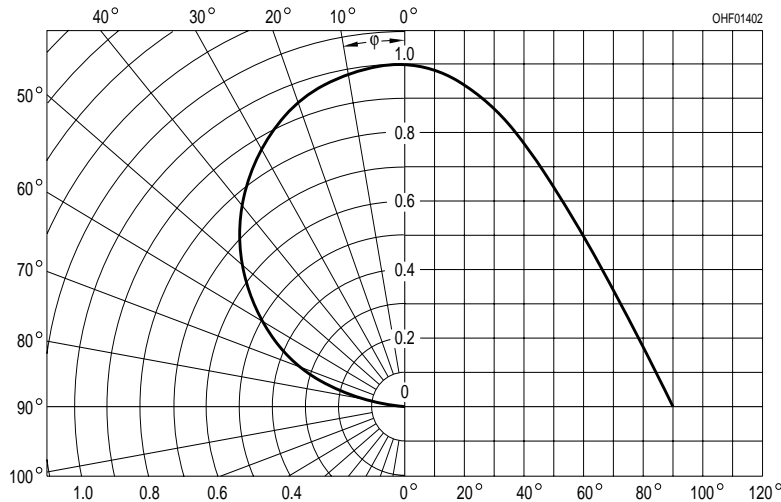
The phototransistors are grouped according to their spectral sensitivity and distinguished by arabian figures.

Bezeichnung Parameter	Symbol Symbol	Wert Value				Einheit Unit
		SFH 320 /FA	-2	-3	-4	
Fotostrom, $\lambda = 950 \text{ nm}$ Photocurrent $E_e = 0.1 \text{ mW/cm}^2, V_{CE} = 5 \text{ V}$ SFH 320: $E_v = 1000 \text{ lx}$, Normlicht/standard light A, $V_{CE} = 5 \text{ V}$	I_{PCE}	≥ 16	16 ... 32	25 ... 50	40 ... 80	μA
	I_{PCE}	–	420	650	1000	μA
Anstiegszeit/Abfallzeit Rise and fall time $I_C = 1 \text{ mA}, V_{CC} = 5 \text{ V}, R_L = 1 \text{ k}\Omega$	t_r, t_f	7	6	7	8	μs
Kollektor-Emitter-Sättigungsspannung Collector-emitter saturation voltage $I_C = I_{PCEmin}^{1)} \times 0.3,$ $E_e = 0.1 \text{ mW/cm}^2$	V_{CEsat}	150	150	150	150	mV

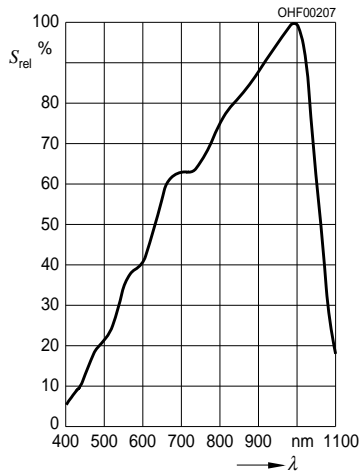
1) I_{PCEmin} ist der minimale Fotostrom der jeweiligen Gruppe.

1) I_{PCEmin} is the min. photocurrent of the specified group.

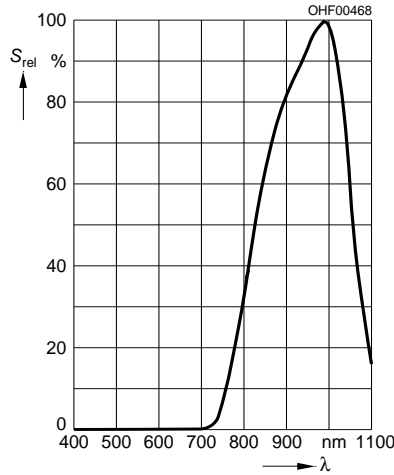
Directional Characteristics $S_{rel} = f(\varphi)$



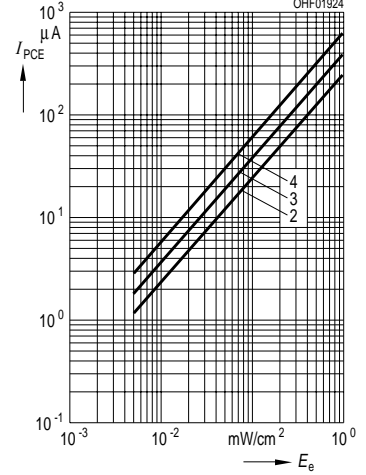
Relative Spectral Sensitivity, SFH 320 $S_{rel} = f(\lambda)$



Relative Spectral Sensitivity, SFH 320 FA $S_{rel} = f(\lambda)$

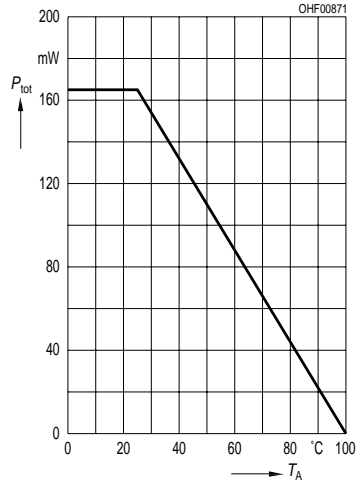


Photocurrent $I_{PCE} = f(E_e), V_{CE} = 5 V$



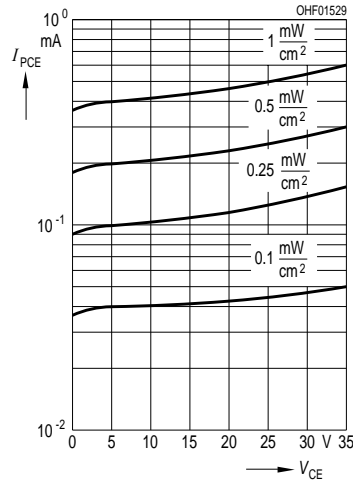
Total Power Dissipation

$P_{tot} = f(T_A)$



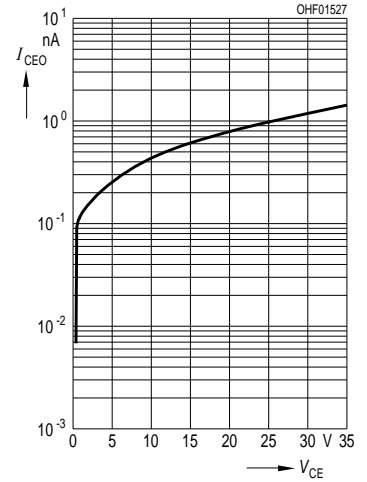
Photocurrent

$I_{PCE} = f(V_{CE}), E_e = \text{Parameter}$



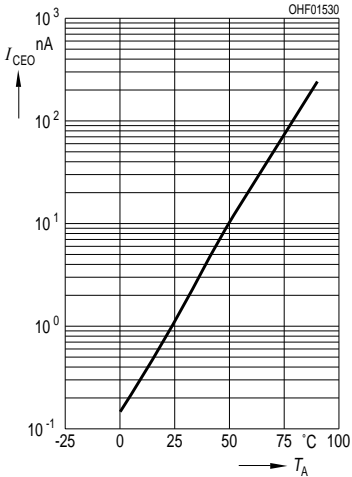
Dark Current

$I_{CEO} = f(V_{CE}), E = 0$



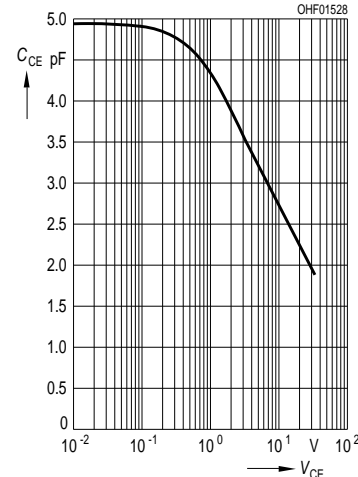
Dark Current

$I_{CEO} = f(T_A), V_{CE} = 5 V, E = 0$



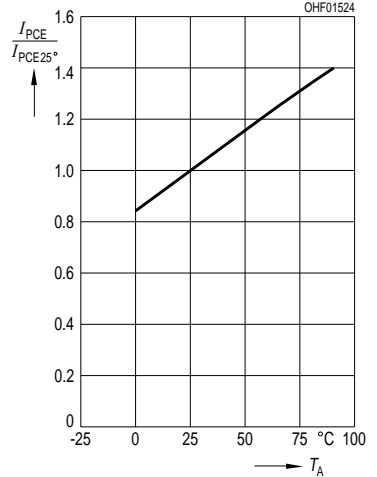
Capacitance

$C_{CE} = f(V_{CE}), f = 1 \text{ MHz}, E = 0$

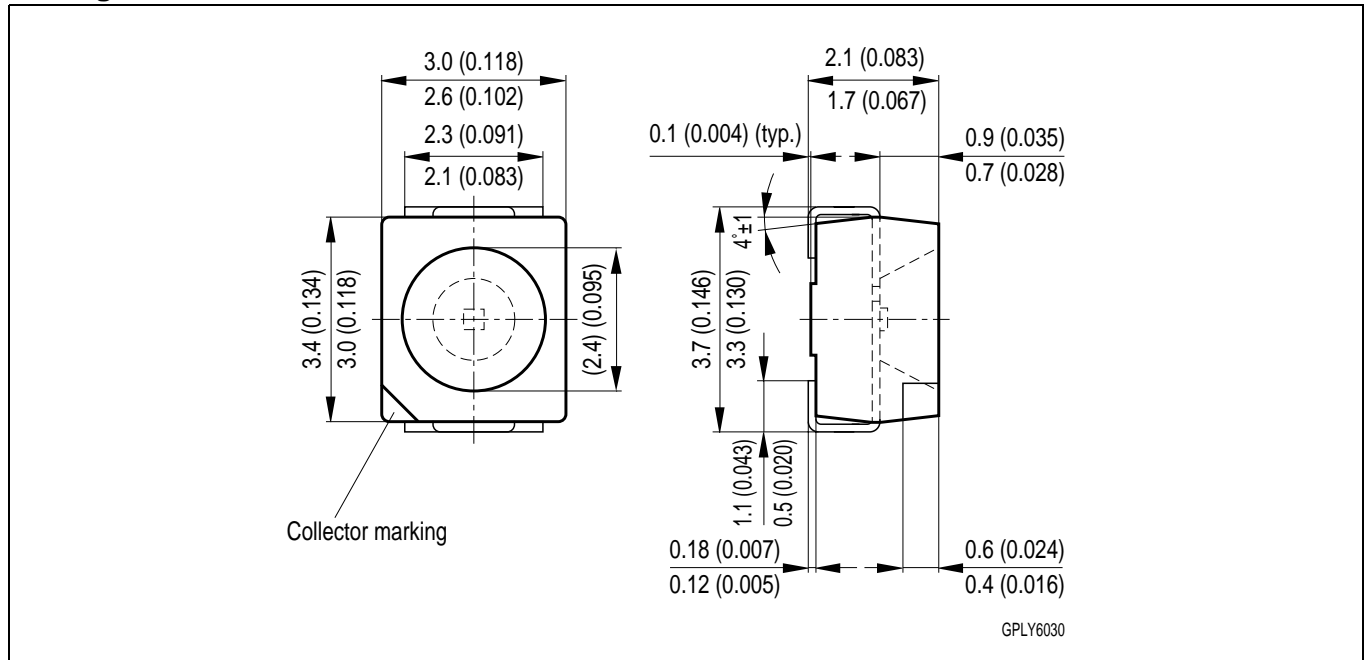


Photocurrent

$I_{PCE}/I_{PCE25} = f(T_A), V_{CE} = 5 V$

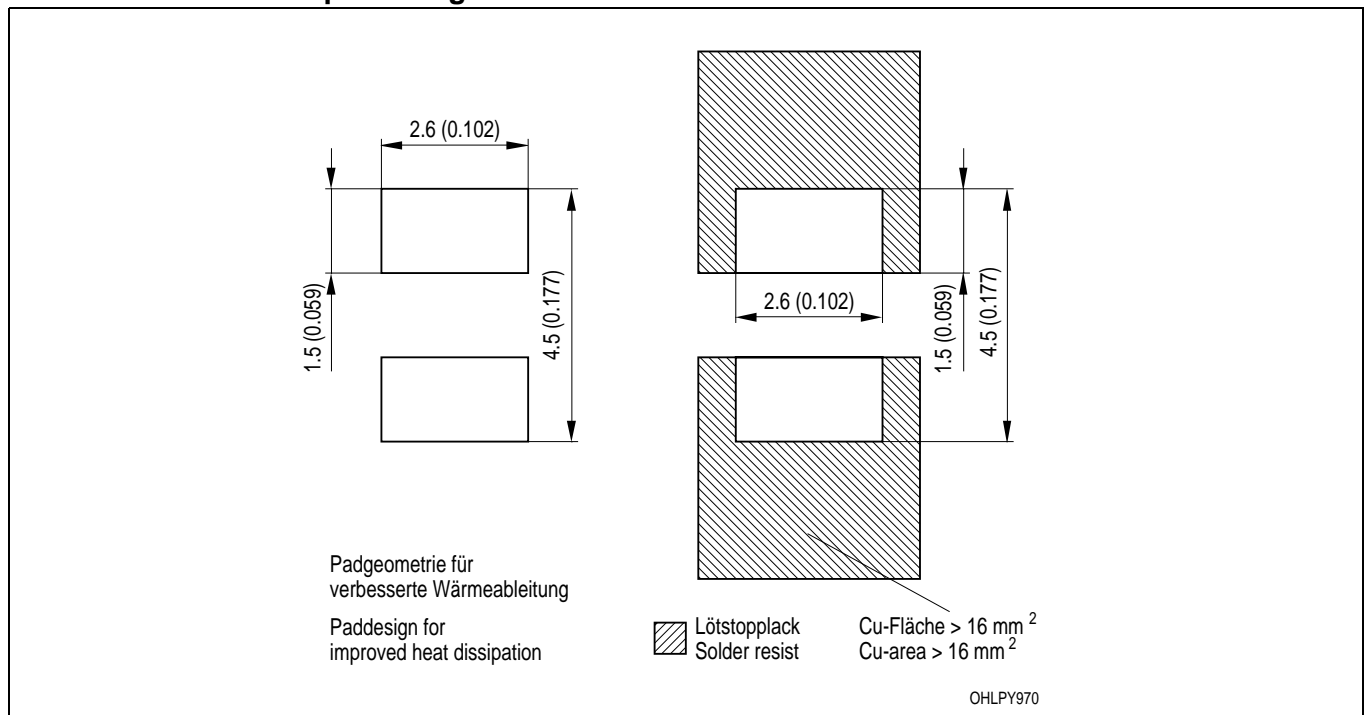


**Maßzeichnung
Package Outlines**



Maße werden wie folgt angegeben: mm (inch) / Dimensions are specified as follows: mm (inch).

**Empfohlenes Lötpad-Design
Recommended Solderpad Design**



Maße werden wie folgt angegeben: mm (inch) / Dimensions are specified as follows: mm (inch).

Lötbedingungen

Soldering Conditions

IR-Reflow Lötprofil für bleifreies Löt

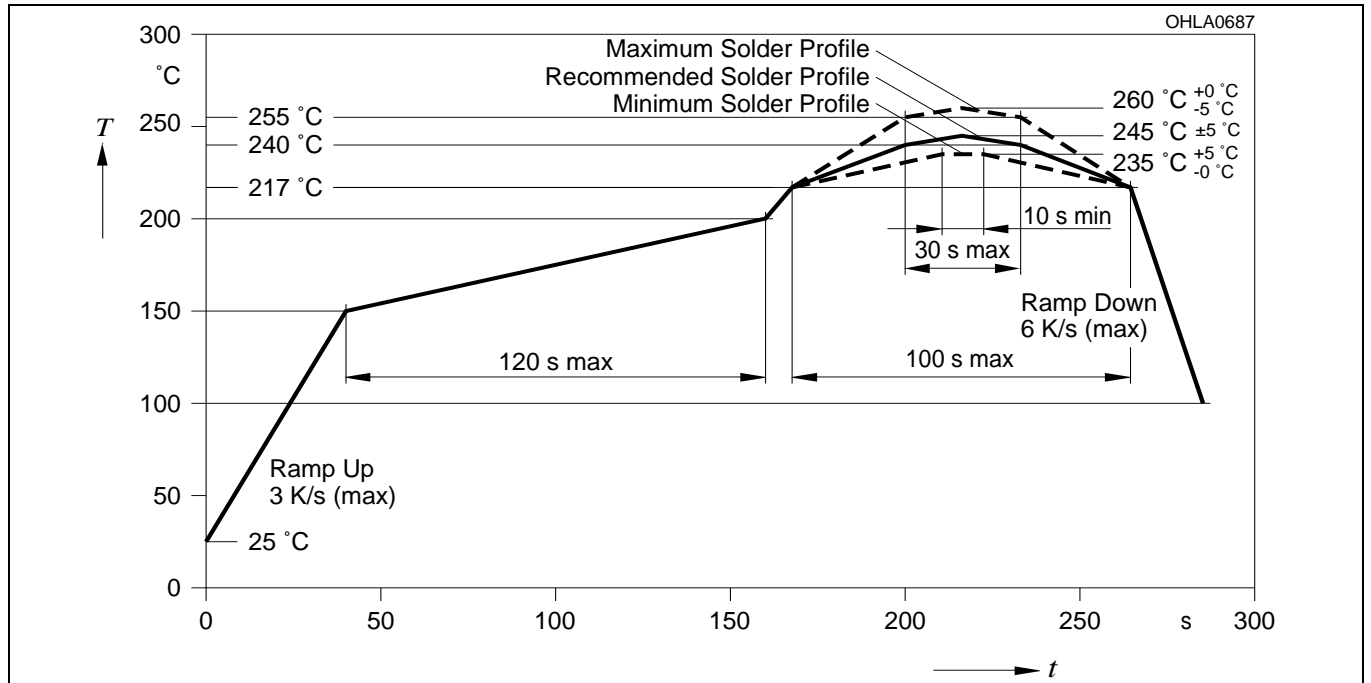
IR Reflow Soldering Profile for lead free soldering

Vorbehandlung nach JEDEC Level 2

Preconditioning acc. to JEDEC Level 2

(nach J-STD-020B)

(acc. to J-STD-020B)

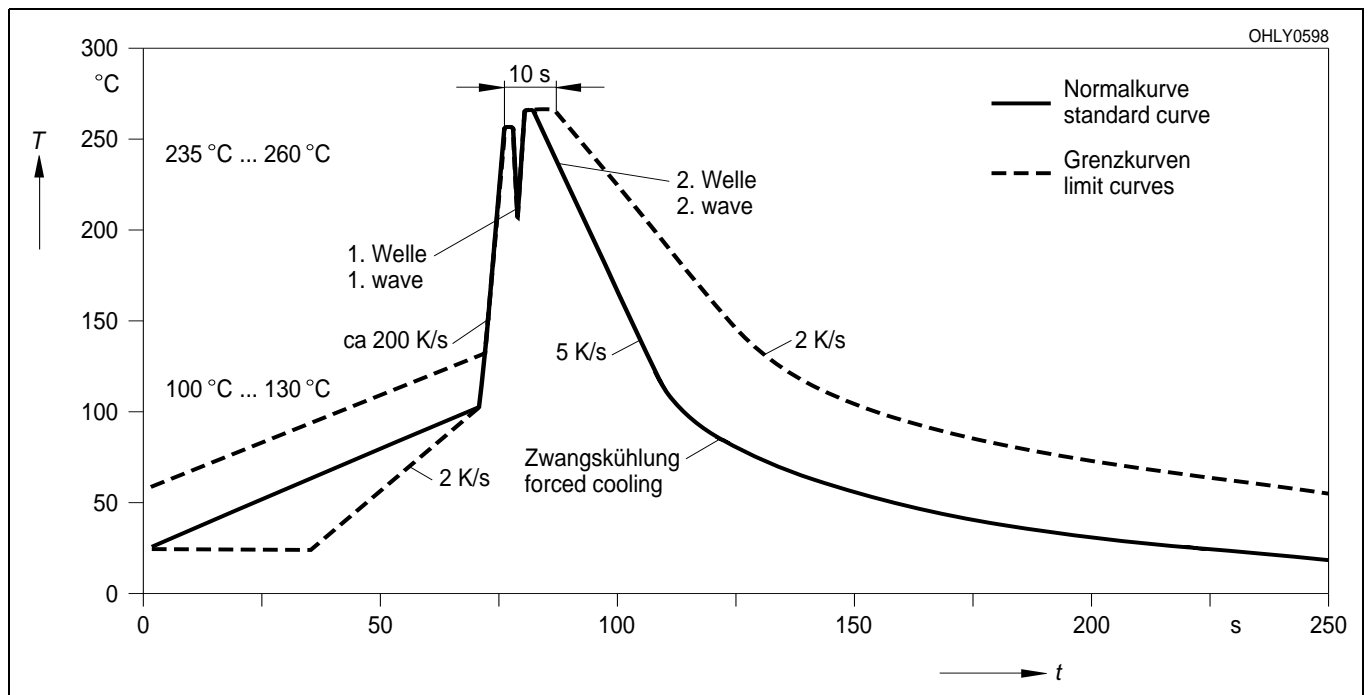


Wellenlöt (TTW)

(nach CECC 00802)

TTW Soldering

(acc. to CECC 00802)



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